

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ max}$	$I_D \text{ max}$ $T_A = +25^\circ\text{C}$
-250V	14Ω @ $V_{GS} = -10\text{V}$	-197mA
	18Ω @ $V_{GS} = -3.5\text{V}$	-175mA

Description

This 250V enhancement mode P-channel MOSFET provides users with a competitive specification. It offers efficient power handling capability, high impedance and is free from thermal runaway and thermally induced secondary breakdown. Applications benefiting from this device include a variety of Telecom and general high voltage circuits.

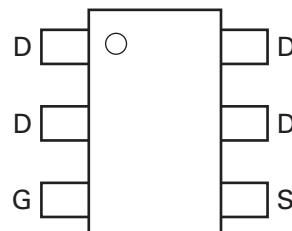
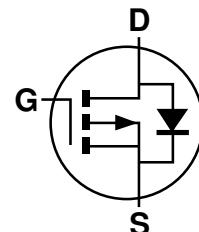
SOT89 and SOT223 versions are also available.

Applications

- Earth Recall and Dialing Switches
- Electronic Hook Switches
- High Voltage Power MOSFET Drivers
- Telecom Call Routers
- Solid State Relays



Top View


 Top View
Pin-Out


Equivalent Circuit

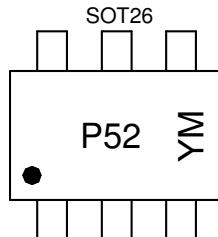
Ordering Information (Note 4)

Part Number	Case	Quantity per reel
ZVP4525E6TA	SOT26	3,000
ZVP4525E6TC	SOT26	3,000

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



P52 = Product Type Marking Code

YM = Date Code Marking

 Y or \bar{Y} = Year (ex: C = 2015)

 M or \bar{M} = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022
Code	C	D	E	F	G	H	I	J

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-250	V
Gate-Source Voltage			V_{GS}	± 40	V
Continuous Drain Current	$V_{GS} = 10\text{V}$	(Note 5)	I_D	-197	mA
		$T_A = +70^\circ\text{C}$ (Note 5)		-157	
Pulsed Drain Current	$V_{GS} = 10\text{V}$	(Note 7)	I_{DM}	-1	A
Continuous Source Current (Body Diode)			I_S	-0.75	A
Pulsed Source Current (Body Diode)			I_{SM}	-1	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

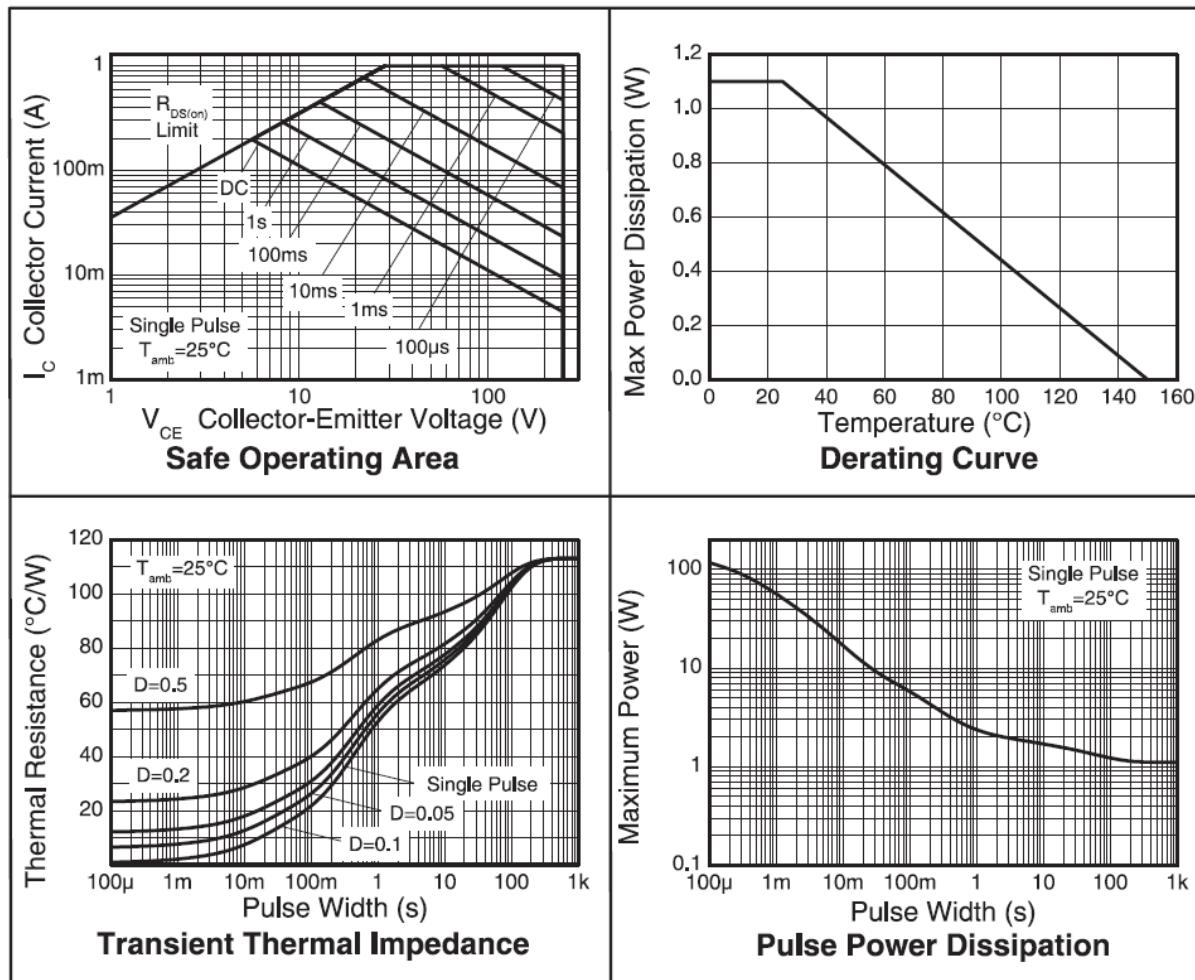
Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P_D	1.1	W
Linear Derating Factor			8.8	$\text{mW}/^\circ\text{C}$
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	113	$^\circ\text{C}/\text{W}$
	(Note 6)		68	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes:

5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
6. For a device surface mounted on FR4 PCB measured at $t \leq 5$ secs.
7. Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

NB High Voltage Applications

For high voltage applications, the appropriate industry sector guidelines should be considered with regard to voltage spacing between conductors.

Thermal Characteristics


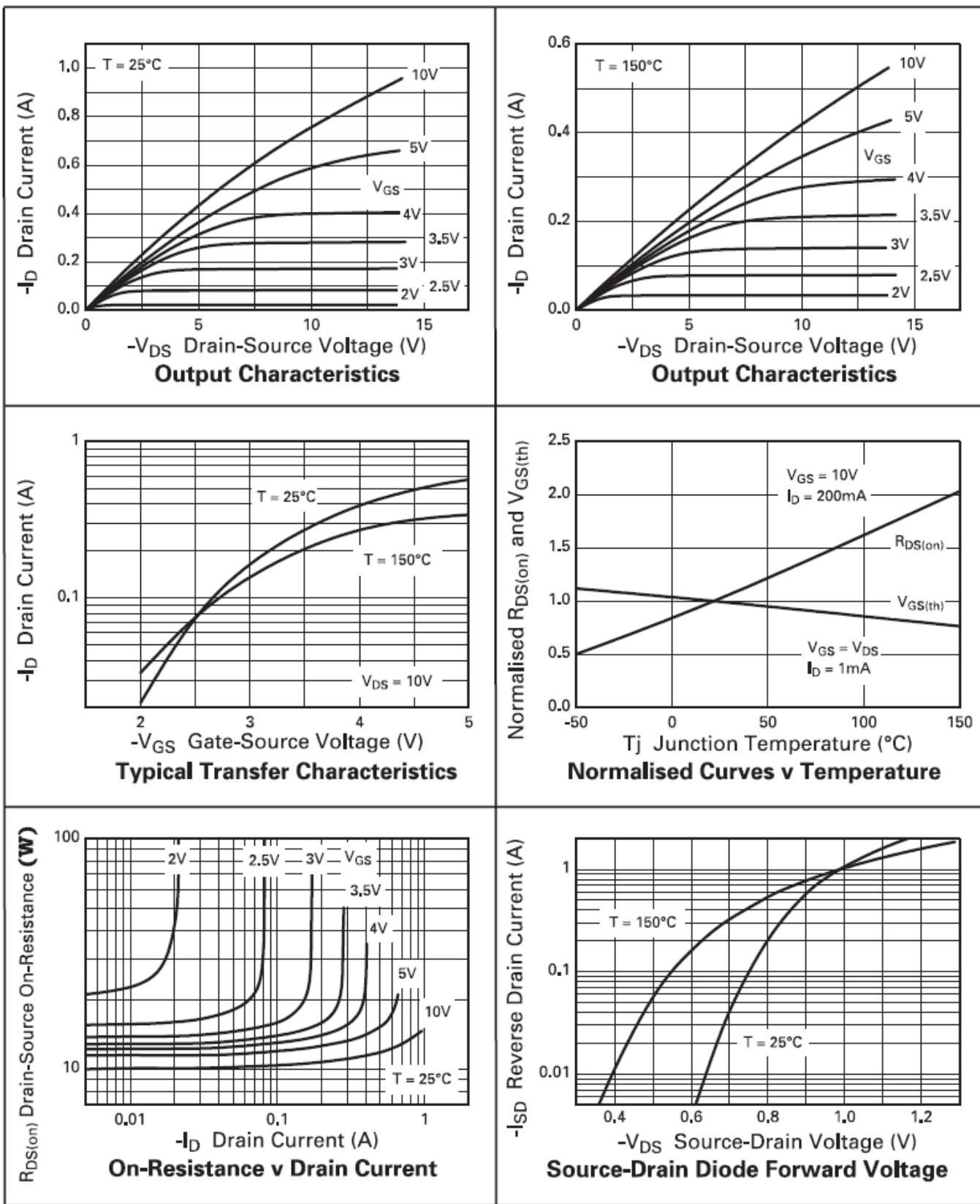
Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	-250	-285	—	V	$I_D = -1\text{mA}$, $V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}	—	-30	-500	nA	$V_{DS} = -250\text{V}$, $V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	± 1	± 100	nA	$V_{GS} = \pm 40\text{V}$, $V_{DS} = 0\text{V}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(\text{th})}$	-0.8	-1.5	-2.0	V	$I_D = -1\text{mA}$, $V_{DS} = V_{GS}$
Static Drain-Source On-Resistance (Note 8)	$R_{DS(\text{ON})}$	—	10	14	Ω	$V_{GS} = -10\text{V}$, $I_D = -200\text{mA}$
		—	13	18		$V_{GS} = -3.5\text{V}$, $I_D = -100\text{mA}$
Forward Transconductance (Notes 10)	g_{fs}	80	200	—	mS	$V_{DS} = -10\text{V}$, $I_D = -0.15\text{A}$
Diode Forward Voltage (Note 9)	V_{SD}	—	-0.86	-0.97	V	$I_S = -200\text{mA}$, $V_{GS} = 0\text{V}$, $T_J = +25^\circ\text{C}$
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	—	73	—	pF	$V_{DS} = -25\text{V}$, $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	12.8	—		
Reverse Transfer Capacitance	C_{rss}	—	3.91	—		
Total Gate Charge (Note 9)	Q_g	—	2.45	2.45	nC	$V_{DS} = -25\text{V}$, $V_{GS} = -10\text{V}$, $I_D = -200\text{mA}$ (refer to test circuit)
Gate-Source Charge (Note 9)	Q_{gs}	—	0.22	0.31		
Gate-Drain Charge (Note 9)	Q_{gd}	—	0.45	0.63		
Turn-On Delay Time (Note 9)	$t_{D(\text{on})}$	—	1.53	—	ns	$V_{DD} = -30\text{V}$, $V_{GS} = -10\text{V}$ $I_D = -200\text{mA}$, $R_G = 50\Omega$ (refer to test circuit)
Turn-On Rise Time (Note 9)	t_r	—	3.78	—		
Turn-Off Delay Time (Note 9)	$t_{D(\text{off})}$	—	17.5	—		
Turn-Off Fall Time (Note 9)	t_f	—	7.85	—		
Reverse Recovery Time	t_{rr}	—	205	290	ns	$I_F = -200\text{mA}$, $di/dt = 100\text{A}/\mu\text{s}$, $T_J = +25^\circ\text{C}$
Reverse Recovery Charge	Q_{rr}	—	21	29	nC	

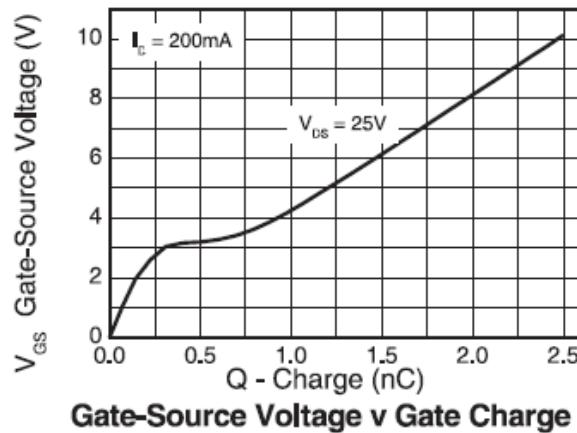
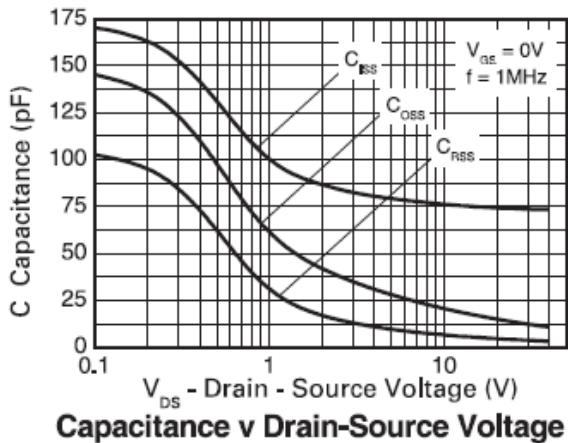
Notes:

- 8. Measured under pulsed conditions. Width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$.
- 9. Switching characteristics are independent of operating junction temperatures.
- 10. For design aid only, not subject to production testing.

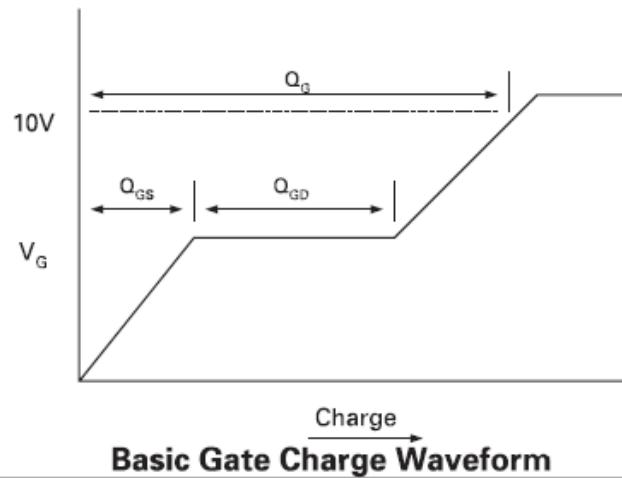
Typical Characteristics



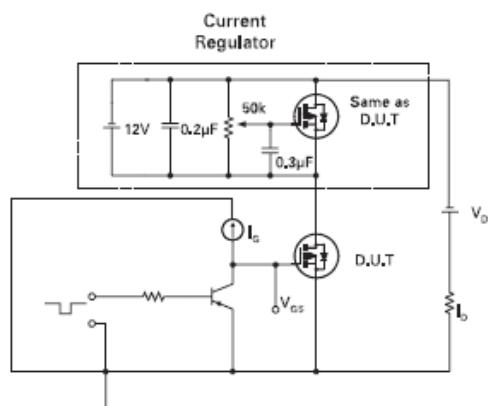
Typical Characteristics (continued)



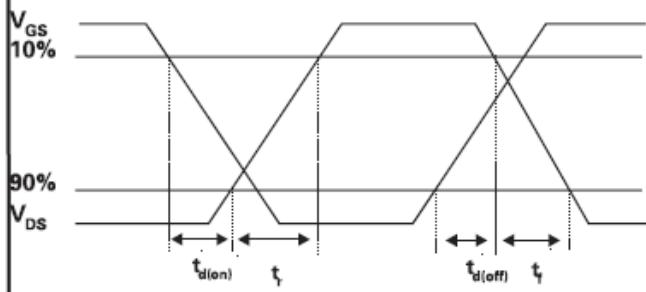
Test Circuits



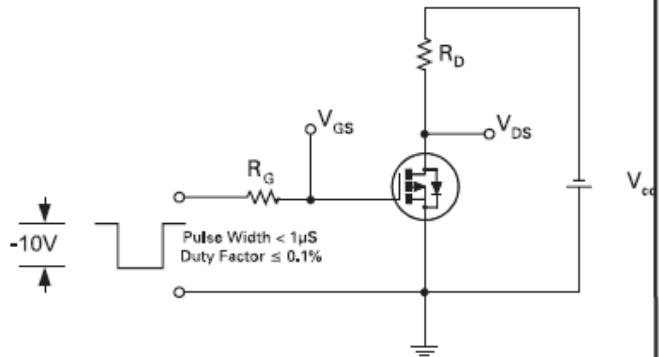
Basic Gate Charge Waveform



Gate Charge Test Circuit



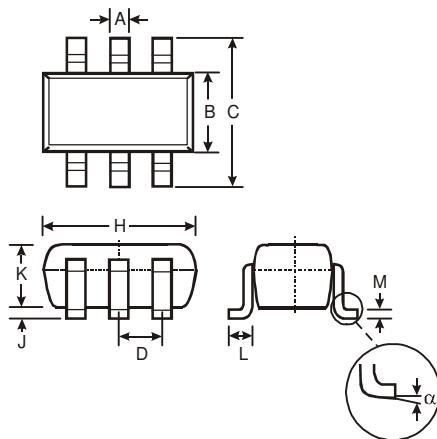
Switching Time Waveforms



Switching Time Test Circuit

Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

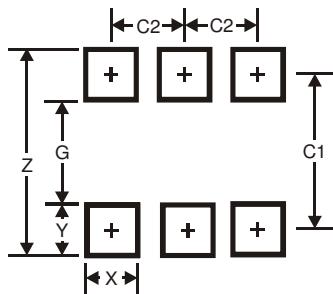


SOT26			
Dim	Min	Max	Typ
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	—	—	0.95
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
α	0°	8°	—

All Dimensions in mm

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
X	0.55
Y	0.80
C1	2.40
C2	0.95

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